



VERSION WITH MARKINGS TO SHOW CHANGES MADE S.N. 09/478,508

IN THE CLAIMS:

Claim 16 has been amended as follows:

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1 16. (Amended) A semiconductor device having a semiconductor chip,
2 first electrodes formed on said semiconductor chip,
3 barrier metals formed on said first electrodes and having laminated structures, and
4 a plurality of second protruded electrodes, which serve as external connection terminals, formed
5 on said barrier metals, wherein said barrier metals comprising:
6 a lowermost conductive metal layer laminated on said first electrodes, said lowermost
7 conductive metal layer having a joining property with said first electrodes;
8 an intermediate conductive metal layer laminated on said lowermost conductive metal layer,
9 said intermediate conductive metal layer being made of nickel (Ni); and
10 an uppermost conductive metal layer laminated on said ~~one or more~~ intermediate
11 conductive metal ~~layers~~ layer, said uppermost conductive metal layer being made of a material which easily
12 alloys with ~~the material~~ the nickel of said intermediate conductive metal ~~layers~~ layer and which has
13 resistance to oxidation, said uppermost conductive metal layer being made of a metal selected from the
14 group consisting of ~~gold (Au)~~, platinum (Pt), palladium (Pd), silver (Ag) and rhodium (Rh) or of an alloy
15 containing a metal selected from the group consisting of gold (Au), platinum (Pt), palladium (Pd), silver (Ag)
16 and rhodium (Rh).